

~~4. (Amended) A silicon/silicon carbide composite according to claim 1, said silicon/silicon carbide composite includes a semiconductor heat treatment member.~~

8. (Amended) A process for manufacturing a silicon/silicon carbide composite according to claim 6, wherein the length of each cellulose fiber is 1.5 mm or more.

9. (Amended) A process for manufacturing a silicon/silicon carbide composite according to claim 6, wherein said cellulose fiber is paper pulp.

11. (Amended) A process for manufacturing a silicon/silicon carbide composite according to claim 6, wherein the bulk density of the porous carbon body produced by said first step is 0.70 g/cm<sup>3</sup> or less.

12. (Amended) A process for manufacturing a silicon/silicon carbide composite according to claim 6, in which a silicification treatment in said second step is conducted by either a reaction with fused silicon or a reaction with silicon monoxide gas.

15. (Amended) A process for manufacturing a silicon/silicon carbide composite according to claim 6, wherein the porous carbon body produced by said first step is heated at a temperature of 1100°C to 2000°C in an atmosphere of halogen gas to be purified prior to the second step.

**Please add claims 18 through 29 as follows:**

18. A silicon/silicon carbide composite according to claim 2, wherein said silicon/silicon carbide composite includes a dummy wafer with a silicon carbide film having a thickness of 30 to 150  $\mu\text{m}$  formed on the surface thereof, said dummy wafer having a total thickness of 0.5 to 1 mm.

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cont

19. A silicon/silicon carbide composite according to claim 2, said silicon/silicon carbide composite includes a semiconductor heat treatment member.

Sub 122  
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20. A process for manufacturing a silicon/silicon carbide composite according to claim 7, wherein the length of each cellulose fiber is 1.5 mm or more.

21. A process for manufacturing a silicon/silicon carbide composite according to claim 7, wherein said cellulose fiber is paper pulp.

22. A process for manufacturing a silicon/silicon carbide composite according to claim 7, wherein the bulk density of the porous carbon body produced by said first step is 0.70 g/cm<sup>3</sup> or less.

23. A process for manufacturing a silicon/silicon carbide composite according to claim 10, wherein the bulk density of the porous carbon body produced by said first step is 0.70 g/cm<sup>3</sup> or less.

24. A process for manufacturing a silicon/silicon carbide composite according to claim 7, in which a silicification treatment in said second step is conducted by either a reaction with fused silicon or a reaction with silicon monoxide gas.

25. A process for manufacturing a silicon/silicon carbide composite according to claim 10, in which a silicification treatment in said second step is conducted by either a reaction with fused silicon or a reaction with silicon monoxide gas.

26. A process for manufacturing a silicon/silicon carbide composite according to claim 7, wherein the porous carbon body produced by said first step is heated at a temperature of 1100°C to 2000°C in an atmosphere of halogen gas to be purified prior to the second step.